

PLUS Search Results for S/N 10689792, Searched February 21, 2006

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5019530
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5851912
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Titles of Most Frequently Occurring Classifications of Patents Returned
From A Search of 10689792 on February 21, 2006

5 438/624 (2 OR, 3 XR)
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS

438/584 COATING WITH ELECTRICALLY OR THERMALLY
CONDUCTIVE MATERIAL

438/597 .To form ohmic contact to semiconductive
material

438/618 ..Contacting multiple semiconductive regions
(i.e., interconnects)

438/622 ...Multiple metal levels, separated by
insulating layer (i.e., multiple level metallization)

438/624Separating insulating layer is laminate or
composite of plural insulating materials

4 428/433 (0 OR, 4 XR)
Class 428 : STOCK MATERIAL OR MISCELLANEOUS ARTICLES

428/411.1 COMPOSITE (NONSTRUCTURAL LAMINATE)

428/426 .Of quartz or glass

428/432 ..Next to metal or compound thereof

428/433 ...Alloy or free metal

4 428/461 (1 OR, 3 XR)
Class 428 : STOCK MATERIAL OR MISCELLANEOUS ARTICLES

428/411.1 COMPOSITE (NONSTRUCTURAL LAMINATE)

428/457 .Of metal

428/461 ..Next to addition polymer from unsaturated
monomers

4 438/637 (0 OR, 4 XR)
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS

438/584 COATING WITH ELECTRICALLY OR THERMALLY
CONDUCTIVE MATERIAL

438/597 .To form ohmic contact to semiconductive
material

438/618 ..Contacting multiple semiconductive regions
(i.e., interconnects)

438/622 ...Multiple metal levels, separated by
insulating layer (i.e., multiple level metallization)

438/637With formation of opening (i.e., viahole)
in insulative layer

3 257/758 (1 OR, 2 XR)
Class 257 : ACTIVE SOLID-STATE DEVICES

257/734 COMBINED WITH ELECTRICAL CONTACT OR LEAD

257/741 .Of specified material other than unalloyed
aluminum

257/750 ..Layered

257/758 ...Multiple metal levels on semiconductor,
separated by insulating layer (e.g., multiple level
metallization for integrated circuit)

3 257/E21.162 (0 OR, 3 XR)
Class 257 : ACTIVE SOLID-STATE DEVICES

257/E21.001 PROCESSES OR APPARATUS ADAPTED FOR MANUFACTURE
OR TREATMENT OF SEMICONDUCTOR OR SOLID-STATE
DEVICES OR OF
PARTS THEREOF (EPO)

257/E21.002 .Manufacture or treatment of semiconductor

257/E21.04 ..Device having at least one potential-jump
 depletion barrier or surface barrier, e.g., PN junction,
 layer, carrier concentration layer (EPO)
 257/E21.085 ...Device having semiconductor body comprising
 without Group IV elements or Group III-V compounds with or
 impurities, e.g., doping materials (EPO)
 257/E21.158Manufacture of electrode on semiconductor
 materials, or body using process other than by epitaxial growth,
 diffusion of impurities, alloying of impurity
 257/E21.159radiation bombardment (EPO)
 (EPO)Deposition of conductive or insulating
 material for electrode conducting electric current
 257/E21.16From a gas or vapor, e.g., condensation
 (EPO)
 257/E21.161Of conductive layer (EPO)
 257/E21.162On semiconductor body comprising Group
 IV element (EPO)

3 257/E21.245 (0 OR, 3 XR)
 Class 257 : ACTIVE SOLID-STATE DEVICES
 257/E21.001 PROCESSES OR APPARATUS ADAPTED FOR MANUFACTURE
 OR TREATMENT OF SEMICONDUCTOR OR SOLID-STATE
 DEVICES OR OF
 PARTS THEREOF (EPO)
 257/E21.002 .Manufacture or treatment of semiconductor
 device (EPO)
 257/E21.04 ..Device having at least one potential-jump
 depletion barrier or surface barrier, e.g., PN junction,
 layer, carrier concentration layer (EPO)
 257/E21.085 ...Device having semiconductor body comprising
 without Group IV elements or Group III-V compounds with or
 impurities, e.g., doping materials (EPO)
 257/E21.211Treatment of semiconductor body using
 material on process other than deposition of semiconductor
 material, or a substrate, diffusion or alloying of impurity
 257/E21.214radiation treatment (EPO)
 cuttingTo change their surface-physical
 characteristics or shape, e.g., etching, polishing,
 (EPO)
 257/E21.24To form insulating layer thereon, e.g.,
 (EPO) for masking or by using photolithographic technique
 257/E21.241Post-treatment (EPO)
 257/E21.243Planarization of insulating layer (EPO)
 257/E21.244Involving dielectric removal step
 (EPO)
 257/E21.245Removal by chemical etching, e.g.,
 dry etching (EPO)

3 257/E21.266 (0 OR, 3 XR)
 Class 257 : ACTIVE SOLID-STATE DEVICES
 Page 2

257/E21.001 PROCESSES OR APPARATUS ADAPTED FOR MANUFACTURE
OR TREATMENT OF SEMICONDUCTOR OR SOLID-STATE
DEVICES OR OF PARTS THEREOF (EPO)

257/E21.002 .Manufacture or treatment of semiconductor
device (EPO)

257/E21.04 ..Device having at least one potential-jump
barrier or surface barrier, e.g., PN junction,
depletion layer, carrier concentration layer (EPO)

257/E21.085 ...Device having semiconductor body comprising
Group IV elements or Group III-V compounds with or
without impurities, e.g., doping materials (EPO)

257/E21.211Treatment of semiconductor body using
process other than deposition of semiconductor
material on a substrate, diffusion or alloying of impurity
material, or radiation treatment (EPO)

257/E21.214To change their surface-physical
characteristics or shape, e.g., etching, polishing,
cutting (EPO)

257/E21.24To form insulating layer thereon, e.g.,
for masking or by using photolithographic technique
(EPO)

257/E21.266Inorganic layer (EPO)

3 257/E21.295 (0 OR, 3 XR)
Class 257 : ACTIVE SOLID-STATE DEVICES

257/E21.001 PROCESSES OR APPARATUS ADAPTED FOR MANUFACTURE
OR TREATMENT OF SEMICONDUCTOR OR SOLID-STATE
DEVICES OR OF PARTS THEREOF (EPO)

257/E21.002 .Manufacture or treatment of semiconductor
device (EPO)

257/E21.04 ..Device having at least one potential-jump
barrier or surface barrier, e.g., PN junction,
depletion layer, carrier concentration layer (EPO)

257/E21.085 ...Device having semiconductor body comprising
Group IV elements or Group III-V compounds with or
without impurities, e.g., doping materials (EPO)

257/E21.211Treatment of semiconductor body using
process other than deposition of semiconductor
material on a substrate, diffusion or alloying of impurity
material, or radiation treatment (EPO)

257/E21.214To change their surface-physical
characteristics or shape, e.g., etching, polishing,
cutting (EPO)

257/E21.294Deposition/post-treatment of
noninsulating, e.g., conductive - or resistive - layers
on insulating layers (EPO)

257/E21.295Deposition of layer comprising metal,
e.g., metal, alloys, metal compounds (EPO)

- 3 257/E21.58 (0 OR, 3 XR)
 Class 257 : ACTIVE SOLID-STATE DEVICES
 257/E21.531 ...For electrical parameters, e.g.,
 resistance, deep-levels, CV, diffusions by
 electrical means
 (EPO)
 257/E21.532 .Manufacture or treatment of devices
 consisting of plurality of solid-state components
 formed in
 or on common substrate or of parts thereof;
 manufacture of
 integrated circuit devices or of parts thereof (EPO)
 257/E21.536 ..Manufacture of specific parts of devices
 (EPO)
 257/E21.575 ...Interconnections, comprising conductors and
 dielectrics, for carrying current between separate
 components within device (EPO)
 257/E21.576Characterized by formation and post
 treatment of dielectrics, e.g., planarizing (EPO)
 257/E21.58Planarizing dielectric (EPO)
- 3 257/E23.145 (0 OR, 3 XR)
 Class 257 : ACTIVE SOLID-STATE DEVICES
 257/E23.139 ...Liquid at normal operating temperature of
 device (EPO)
 257/E23.141 .Arrangements for conducting electric current
 within device in operation from one component to
 another,
 interconnections, e.g., wires, lead frames (EPO)
 257/E23.142 ..Including external interconnections
 consisting of multilayer structure of conductive and
 insulating layers inseparably formed on semiconductor
 body
 (EPO)
 257/E23.145 ...Via connections in multilevel
 interconnection structure (EPO)
- 3 428/209 (0 OR, 3 XR)
 Class 428 : STOCK MATERIAL OR MISCELLANEOUS ARTICLES
 428/98 STRUCTURALLY DEFINED WEB OR SHEET (E.G.,
 OVERALL DIMENSION, ETC.)
 428/195.1 .Discontinuous or differential coating,
 impregnation or bond (e.g., artwork, printing, retouched
 photograph, etc.)
 428/209 ..Including metal layer
- 3 428/35.9 (1 OR, 2 XR)
 Class 428 : STOCK MATERIAL OR MISCELLANEOUS ARTICLES
 428/34.1 HOLLOW OR CONTAINER TYPE ARTICLE (E.G., TUBE,
 VASE, ETC.)
 428/35.7 .Polymer or resin containing (i.e., natural or
 synthetic)
 428/35.8 ..Elemental metal containing (e.g., substrate,
 foil, film, coating, etc.)
 428/35.9 ...Three or more layers (continuous layer)
- 2 117/108 (0 OR, 2 XR)
 Class 117 : SINGLE-CRYSTAL, ORIENTED-CRYSTAL, AND EPITAXY
 GROWTH PROCESSES; NON-COATING APPARATUS THEREFOR
 117/84 FORMING FROM VAPOR OR GASEOUS STATE (E.G., VPE,
 SUBLIMATION)
 117/108 .Using an energy beam or field, a particle beam
 or field, or a plasma (e.g., MBE)

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- 2 117/940 (0 OR, 2 XR)
 Class 117 : SINGLE-CRYSTAL, ORIENTED-CRYSTAL, AND EPITAXY
 GROWTH PROCESSES; NON-COATING APPARATUS THEREFOR
 117/937 INORGANIC CONTAINING SINGLE-CRYSTAL (E.G.,
 COMPOUND, MIXTURE, COMPOSITE) {C30B 29/10}
 117/940 .Halide containing (e.g., fluorphlogopite,
 fluor-mica) {C30B 29/12}
- 2 118/308 (0 OR, 2 XR)
 Class 118 : COATING APPARATUS
 118/300 PROJECTION OR SPRAY TYPE
 118/308 .Applying solid particulate material
- 2 118/323 (0 OR, 2 XR)
 Class 118 : COATING APPARATUS
 118/300 PROJECTION OR SPRAY TYPE
 118/323 .Moving projector
- 2 118/59 (1 OR, 1 XR)
 Class 118 : COATING APPARATUS
 118/58 WITH HEAT EXCHANGE, DRYING, OR NON-COATING GAS
 OR VAPOR TREATMENT OF WORK
 118/59 .With solid heat exchange means contacting work
- 2 118/673 (0 OR, 2 XR)
 Class 118 : COATING APPARATUS
 118/663 CONTROL MEANS RESPONSIVE TO A RANDOMLY
 OCCURRING SENSED CONDITION
 118/668 .Responsive to attribute, absence or presence
 of work
 118/672 ..Running length work
 118/673 ...Edge of running length of web material
 sensed
- 2 118/69 (0 OR, 2 XR)
 Class 118 : COATING APPARATUS
 118/58 WITH HEAT EXCHANGE, DRYING, OR NON-COATING GAS
 OR VAPOR TREATMENT OF WORK
 118/69 .Cooling
- 2 148/33.4 (1 OR, 1 XR)
 Class 148 : METAL TREATMENT
 148/33 BARRIER LAYER STOCK MATERIAL, P-N TYPE
 148/33.4 .With contiguous layers of different
 semiconductive material
- 2 148/33.5 (0 OR, 2 XR)
 Class 148 : METAL TREATMENT
 148/33 BARRIER LAYER STOCK MATERIAL, P-N TYPE
 148/33.5 .Having at least three contiguous layers of
 semiconductive material
- 2 216/13 (1 OR, 1 XR)
 Class 216 : ETCHING A SUBSTRATE: PROCESSES
 216/13 FORMING OR TREATING ELECTRICAL CONDUCTOR
 ARTICLE (E.G., CIRCUIT, ETC.)
- 2 220/62.12 (2 OR, 0 XR)
 Class 220 : RECEPTACLES
 220/62.11 RECEPTACLE SIDE WALL MADE OF TWO OR MORE LAYERS
 OF MATERIAL PERMANENTLY ATTACHED TOGETHER

220/62.12 .Beverage receptacle

- 2 220/669 (0 OR, 2 XR)
 Class 220 : RECEPTACLES
 220/660 SIDEWALL STRUCTURE
 220/669 .Contoured sidewall (e.g., curved, corrugated,
 ribbed, variable thickness, etc.)
- 2 228/121 (1 OR, 1 XR)
 Class 228 : METAL FUSION BONDING
 228/101 PROCESS
 228/121 .Bonding nonmetals with metallic filler
- 2 228/122.1 (0 OR, 2 XR)
 Class 228 : METAL FUSION BONDING
 228/101 PROCESS
 228/122.1 .Metal to nonmetal with separate metallic
 filler
- 2 228/124.1 (0 OR, 2 XR)
 Class 228 : METAL FUSION BONDING
 228/101 PROCESS
 228/122.1 .Metal to nonmetal with separate metallic
 filler
 228/124.1 ..With treating
- 2 228/195 (1 OR, 1 XR)
 Class 228 : METAL FUSION BONDING
 228/101 PROCESS
 228/193 .Diffusion type
 228/195 ..With incipient melting of bonding surface
- 2 257/750 (0 OR, 2 XR)
 Class 257 : ACTIVE SOLID-STATE DEVICES
 257/734 COMBINED WITH ELECTRICAL CONTACT OR LEAD
 257/741 .Of specified material other than unalloyed
 aluminum
 257/750 ..Layered
- 2 257/751 (0 OR, 2 XR)
 Class 257 : ACTIVE SOLID-STATE DEVICES
 257/734 COMBINED WITH ELECTRICAL CONTACT OR LEAD
 257/741 .Of specified material other than unalloyed
 aluminum
 257/750 ..Layered
 257/751 ...At least one layer forms a diffusion barrier
- 2 257/761 (0 OR, 2 XR)
 Class 257 : ACTIVE SOLID-STATE DEVICES
 257/734 COMBINED WITH ELECTRICAL CONTACT OR LEAD
 257/741 .Of specified material other than unalloyed
 aluminum
 257/750 ..Layered
 257/761 ...At least one layer containing vanadium,
 hafnium, niobium, zirconium, or tantalum
- 2 257/769 (0 OR, 2 XR)
 Class 257 : ACTIVE SOLID-STATE DEVICES
 257/734 COMBINED WITH ELECTRICAL CONTACT OR LEAD
 257/741 .Of specified material other than unalloyed
 aluminum
 257/768 ..Refractory or platinum group metal or alloy

or silicide thereof

257/769 ...Platinum group metal or silicide thereof

2 257/E21.585 (0 OR, 2 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

257/E21.531 ...For electrical parameters, e.g.,
resistance, deep-levels, CV, diffusions by

electrical means

(EPO)

257/E21.532 .Manufacture or treatment of devices
consisting of plurality of solid-state components

formed in

or on common substrate or of parts thereof;

manufacture of

integrated circuit devices or of parts thereof (EPO)

257/E21.536 ..Manufacture of specific parts of devices
(EPO)257/E21.575 ...Interconnections, comprising conductors and
dielectrics, for carrying current between separate
components within device (EPO)257/E21.576Characterized by formation and post
treatment of dielectrics, e.g., planarizing (EPO)257/E21.585Filling of holes, grooves, vias or
trenches with conductive material (EPO)

2 257/E21.59 (0 OR, 2 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

257/E21.531 ...For electrical parameters, e.g.,
resistance, deep-levels, CV, diffusions by

electrical means

(EPO)

257/E21.532 .Manufacture or treatment of devices
consisting of plurality of solid-state components

formed in

or on common substrate or of parts thereof;

manufacture of

integrated circuit devices or of parts thereof (EPO)

257/E21.536 ..Manufacture of specific parts of devices
(EPO)257/E21.575 ...Interconnections, comprising conductors and
dielectrics, for carrying current between separate
components within device (EPO)257/E21.576Characterized by formation and post
treatment of dielectrics, e.g., planarizing (EPO)

257/E21.59Local interconnects; local pads (EPO)

2 257/E23.106 (0 OR, 2 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

257/E23.079 ..For integrated circuit devices, e.g., power
bus, number of leads (EPO)257/E23.08 .Arrangements for cooling, heating, ventilating
or temperature compensation; temperature-sensing
arrangements (EPO)257/E23.101 ..Selection of materials, or shaping, to
facilitate cooling or heating, e.g., heat sinks (EPO)257/E23.106 ...Laminates or multilayers, e.g., direct bond
copper ceramic substrates (EPO)

2 257/E23.147 (0 OR, 2 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

257/E23.139 ...Liquid at normal operating temperature of
device (EPO)

257/E23.141 .Arrangements for conducting electric current

another,
 257/E23.142 ..Including external interconnections
 consisting of multilayer structure of conductive and
 insulating layers inseparably formed on semiconductor

body
 (EPO)
 257/E23.146 ...With adaptable interconnections (EPO)
 257/E23.147Comprising antifuses, i.e., connections
 having their state changed from nonconductive to
 conductive
 (EPO)

2 257/E23.167 (0 OR, 2 XR)
 Class 257 : ACTIVE SOLID-STATE DEVICES
 257/E23.139 ...Liquid at normal operating temperature of
 device (EPO)
 257/E23.141 .Arrangements for conducting electric current
 within device in operation from one component to

another,
 257/E23.142 ..Including external interconnections
 consisting of multilayer structure of conductive and
 insulating layers inseparably formed on semiconductor
 body
 (EPO)
 257/E23.154 ...Characterized by materials (EPO)
 257/E23.167Insulating materials (EPO)

2 257/E29.162 (0 OR, 2 XR)
 Class 257 : ACTIVE SOLID-STATE DEVICES
 257/E29.104Si compounds (e.g., SiC) (EPO)
 257/E29.111 .Electrodes (EPO)
 257/E29.139 ..Of specified material (EPO)
 257/E29.15 ...Electrodes for IGFET (EPO)
 257/E29.162Insulating materials for IGFET (EPO)

2 359/586 (0 OR, 2 XR)
 Class 359 : OPTICS: SYSTEMS
 359/577 LIGHT INTERFERENCE
 359/580 .Produced by coating or lamina
 359/586 ..Layers having specified index of refraction

2 427/422 (0 OR, 2 XR)
 Class 427 : COATING PROCESSES
 427/421.1 SPRAYING
 427/422 .Heated coating material

2 427/424 (0 OR, 2 XR)
 Class 427 : COATING PROCESSES
 427/421.1 SPRAYING
 427/424 .Moving the base

2 427/446 (1 OR, 1 XR)
 Class 427 : COATING PROCESSES
 427/446 SPRAY COATING UTILIZING FLAME OR PLASMA HEAT
 (E.G., FLAME SPRAYING, ETC.)

2 428/210 (2 OR, 0 XR)
 Class 428 : STOCK MATERIAL OR MISCELLANEOUS ARTICLES
 428/98 STRUCTURALLY DEFINED WEB OR SHEET (E.G.,

OVERALL DIMENSION, ETC.)

- 428/195.1 .Discontinuous or differential coating,
impregnation or bond (e.g., artwork, printing, retouched
photograph, etc.)
- 428/210 ..Including ceramic, glass, porcelain or quartz
layer
- 2 428/213 (0 OR, 2 XR)
Class 428 : STOCK MATERIAL OR MISCELLANEOUS ARTICLES
428/98 STRUCTURALLY DEFINED WEB OR SHEET (E.G.,
OVERALL DIMENSION, ETC.)
428/212 .Including components having same physical
characteristic in differing degree
428/213 ..Thickness (relative or absolute)
- 2 428/214 (0 OR, 2 XR)
Class 428 : STOCK MATERIAL OR MISCELLANEOUS ARTICLES
428/98 STRUCTURALLY DEFINED WEB OR SHEET (E.G.,
OVERALL DIMENSION, ETC.)
428/212 .Including components having same physical
characteristic in differing degree
428/213 ..Thickness (relative or absolute)
428/214 ...Of adhesive layers
- 2 428/215 (1 OR, 1 XR)
Class 428 : STOCK MATERIAL OR MISCELLANEOUS ARTICLES
428/98 STRUCTURALLY DEFINED WEB OR SHEET (E.G.,
OVERALL DIMENSION, ETC.)
428/212 .Including components having same physical
characteristic in differing degree
428/213 ..Thickness (relative or absolute)
428/215 ...Absolute thicknesses specified
- 2 428/457 (0 OR, 2 XR)
Class 428 : STOCK MATERIAL OR MISCELLANEOUS ARTICLES
428/411.1 COMPOSITE (NONSTRUCTURAL LAMINATE)
428/457 .Of metal
- 2 428/462 (0 OR, 2 XR)
Class 428 : STOCK MATERIAL OR MISCELLANEOUS ARTICLES
428/411.1 COMPOSITE (NONSTRUCTURAL LAMINATE)
428/457 .Of metal
428/461 ..Next to addition polymer from unsaturated
monomers
428/462 ...Including polyene monomers (e.g., butadiene,
etc.)
- 2 428/623 (1 OR, 1 XR)
Class 428 : STOCK MATERIAL OR MISCELLANEOUS ARTICLES
428/544 ALL METAL OR WITH ADJACENT METALS
428/615 .Composite; i.e., plural, adjacent, spatially
distinct metal components (e.g., layers, joint, etc.)
428/621 ..with additional, spatially distinct nonmetal
component
428/622 ...More than one such component
428/623Adjacent to each other
- 2 428/627 (1 OR, 1 XR)
Class 428 : STOCK MATERIAL OR MISCELLANEOUS ARTICLES
428/544 ALL METAL OR WITH ADJACENT METALS
428/615 .Composite; i.e., plural, adjacent, spatially
distinct metal components (e.g., layers, joint, etc.)
428/621 ..with additional, spatially distinct nonmetal

- component
428/627 ...Boride, carbide or nitride component
- 2 428/654 (0 OR, 2 XR)
Class 428 : STOCK MATERIAL OR MISCELLANEOUS ARTICLES
428/544 ALL METAL OR WITH ADJACENT METALS
428/615 .Composite; i.e., plural, adjacent, spatially
distinct metal components (e.g., layers, joint, etc.)
428/650 ..Al-base component
428/654 ...Next to Al-base component
- 2 428/901 (0 OR, 2 XR)
Class 428 : STOCK MATERIAL OR MISCELLANEOUS ARTICLES
428/901 PRINTED CIRCUIT
- 2 438/622 (1 OR, 1 XR)
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
438/584 COATING WITH ELECTRICALLY OR THERMALLY
CONDUCTIVE MATERIAL
438/597 .To form ohmic contact to semiconductive
material
438/618 ..Contacting multiple semiconductive regions
(i.e., interconnects)
438/622 ...Multiple metal levels, separated by
insulating layer (i.e., multiple level metallization)
- 2 438/675 (1 OR, 1 XR)
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
438/584 COATING WITH ELECTRICALLY OR THERMALLY
CONDUCTIVE MATERIAL
438/597 .To form ohmic contact to semiconductive
material
438/674 ..Selective deposition of conductive layer
438/675 ...Plug formation (i.e., in viahole)
- 2 438/699 (0 OR, 2 XR)
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
438/689 CHEMICAL ETCHING
438/694 .Combined with coating step
438/697 ..Planarization by etching and coating
438/699 ...Plural coating steps
- 2 438/763 (0 OR, 2 XR)
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
438/758 COATING OF SUBSTRATE CONTAINING SEMICONDUCTOR
REGION OR OF SEMICONDUCTOR SUBSTRATE
438/761 .Multiple layers
438/763 ..Layers formed of diverse composition or by
diverse coating processes

Most Frequently Occurring Classifications of Patents Returned
From A Search of 10689792 on February 21, 2006

Original Classifications

2 220/62.12
2 428/210
2 438/624

Cross-Reference Classifications

4 428/433
4 438/637
3 257/E21.162
3 257/E21.245
3 257/E21.266
3 257/E21.295
3 257/E21.58
3 257/E23.145
3 428/209
3 428/461
3 438/624
2 117/108
2 117/940
2 118/308
2 118/323
2 118/673
2 118/69
2 148/33.5
2 220/669
2 228/122.1
2 228/124.1
2 257/750
2 257/751
2 257/758
2 257/761
2 257/769
2 257/E21.585
2 257/E21.59
2 257/E23.106
2 257/E23.147
2 257/E23.167
2 257/E29.162
2 359/586
2 427/422
2 427/424
2 428/213
2 428/214
2 428/35.9
2 428/457
2 428/462
2 428/654
2 428/901
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2 438/763

Combined Classifications

5 438/624
4 428/433
4 428/461
4 438/637
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3 257/E21.162
3 257/E21.245

3 257/E21.266
3 257/E21.295
3 257/E21.58
3 257/E23.145
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3 428/35.9
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2 148/33.5
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2 257/E23.106
2 257/E23.147
2 257/E23.167
2 257/E29.162
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2 428/210
2 428/213
2 428/214
2 428/215
2 428/457
2 428/462
2 428/623
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2 428/654
2 428/901
2 438/622
2 438/675
2 438/699
2 438/763